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https://www.centralsemi.com/process-change-notices

PCN # 236 Notification Date: October 4, 2022

# **Product / Process Change Notice**

### **Devices affected:**

The following P-Channel JFETs:

### Part numbers affected:

TO-92 Case	TO-18 Case	TO-72 Case
2N5460	2N2608	2N3330
2N5461		
2N5462		
2N3820		
PN5033		

#### **Extent of change:**

Change in wafer fab, resulting in change in die size from 20 x 20 mils to 18.9 x 18.9 mils (see Table 1).

#### Reason for change:

As part of Central Semiconductor's supply chain risk mitigation initiative, and in an effort to ensure an undisrupted supply of product, a change in wafer fabrication site is being made for the products referenced above. Product specifications, quality and reliability are not impacted by this change.

#### **Effect of change:**

This change does not affect the fit, form or function of the devices.

### **Earliest effective date of change:**

October 4, 2022

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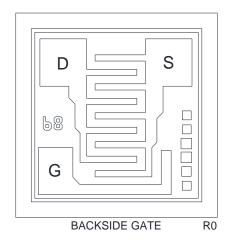


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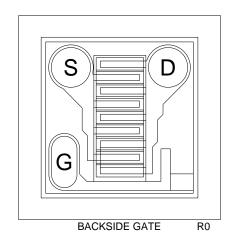
### <u>Table 1</u>:

# **Before Change**



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# **After Change**



20 x 20 MILS	
8.0 MILS	
4.0 x 4.0 MILS	
4.0 x 4.0 MILS	
3.0 x 4.0 MILS	
Al – 30,000Å	
Au – 6,000Å	

Die Size	18.9 x 18.9 MILS	
Die Thickness	7.9 MILS	
Drain Bonding Pad Size	4.2 MILS DIAMETER	
Source Bonding Pad Size	4.2 MILS DIAMETER	
Gate Bonding Pad Size	2.9 x 5.3 MILS	
Top Side Metalization	Al-Si – 17,000Å	
Back Side Metalization	Au – 12,000Å	

# **Qualification data:**

Test	Condition	Failure rate
High Temperature Storage Life/ bake test.	150°C (-0/+10)°C, 1000 hours. <b>JESD22-A103</b>	0/77
Temperature Cycling	T= -65°C to +150°C 1000 cycles. Dwell time = 15 min. <b>JESD22-A104 &amp; MIL-STD-750 TM1051</b>	0/77
High Temperature Gate Bias (HTGB)	T=125°C, t=1000 hours, Bias at V_GS from gate to source with source and drain shorted  JESD22-A108	0/77
Highly Accelerated Temperature and Humidity Stress Test (HAST)	T = 110°C, RH = 85%, and t = 264 hours. Bias conditions per device specification sheet.  JESD22-A110	0/77

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As per JEDEC standard JESD46, Customer Notification of Product/Process Changes by Solid-State Suppliers, a lack of acknowledgement of a PCN within thirty (30) days constitutes acceptance of the change.

The undersigned acknowledges and accepts Central Semiconductor's Product/Process Change Notification (PCN).

Company Name:	
Address:	
Printed Name:	
Title:	
Signature:	
Date:	

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